

The RF Line

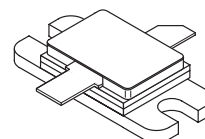
Microwave Long Pulse Power Transistor

Designed for 960–1215 MHz long pulse common base amplifier applications such as JTIDS and Mode S transmitters.

- Guaranteed Performance @ 1.215 GHz, 36 Vdc
Output Power = 120 Watts Peak
Gain = 8.0 dB Min., 9.2 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 3:1 VSWR
- Hermetically Sealed Industry Standard Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input and Output Matching for Broadband Operation
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF10120

**120 W (PEAK), 960–1215 MHz
MICROWAVE POWER
TRANSISTOR
NPN SILICON**



CASE 355C-02, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	55	Vdc
Collector–Base Voltage	V_{CBO}	55	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Peak (1)	I_C	15	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1), (2) Derate above 25°C	P_D	380 2.17	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +200	$^\circ\text{C}$
Junction Temperature	T_J	200	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.46	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 60\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	55	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 36\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	25	mAdc

NOTES:

(continued)

1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.



ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

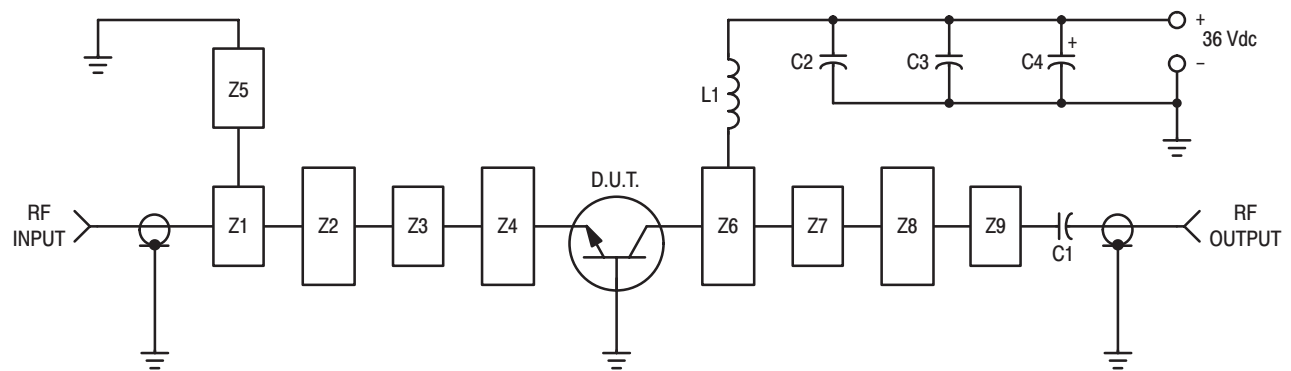
Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	—	—	—
------------------------------------------------------------------------	----------	----	---	---	---

FUNCTIONAL TESTS (7.0 μs Pulses @ 54% duty cycle for 3.4 ms; then off for 4.5 ms; overall duty cycle = 23%)

Common-Base Amplifier Power Gain ($V_{CC} = 36\text{ Vdc}$, $P_{out} = 120\text{ W Peak}$, $f = 1215\text{ MHz}$)	G_{PB}	8.0	9.2	—	dB
Collector Efficiency ($V_{CC} = 36\text{ Vdc}$, $P_{out} = 120\text{ W Peak}$, $f = 1215\text{ MHz}$)	η	50	55	—	%
Load Mismatch ($V_{CC} = 36\text{ Vdc}$, $P_{out} = 120\text{ W Peak}$, $f = 1215\text{ MHz}$, VSWR = 3:1 All Phase Angles)	ψ	No Degradation in Output Power			



C1 — 270 pF 100 Mil Chip Capacitor
C2 — 220 pF 100 Mil Chip Capacitor
C3 — 0.1 μF
C4 — 47 μF 50 V Electrolytic
L1 — 3 Turns #18 AWG, 1/8" ID, 0.18 Long

Z1–Z9 — Microstrip, See Details
Board Material — Teflon®/Glass Laminate,
Dielectric Thickness = 0.030",
 $\epsilon_r = 2.55$, 2 Oz. Copper

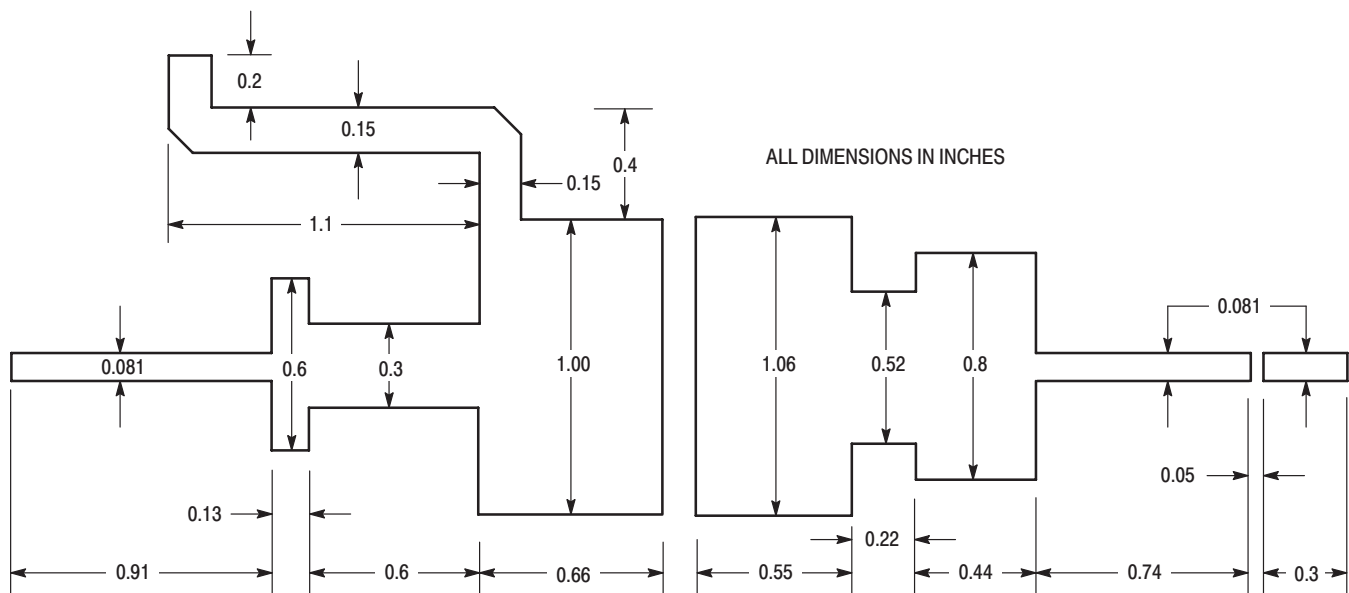


Figure 1. Test Circuit

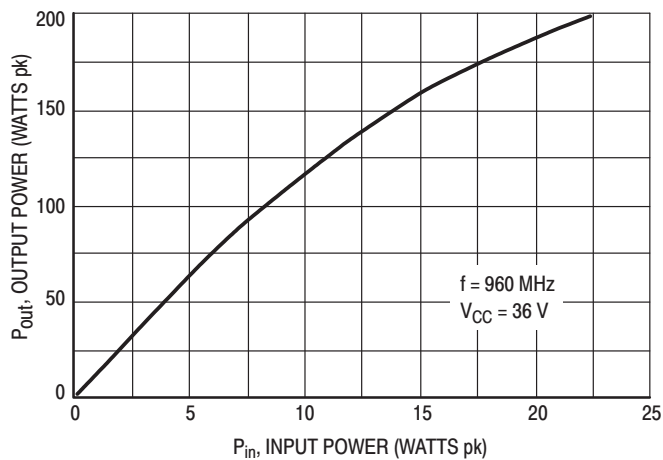


Figure 2. Output Power versus Input Power

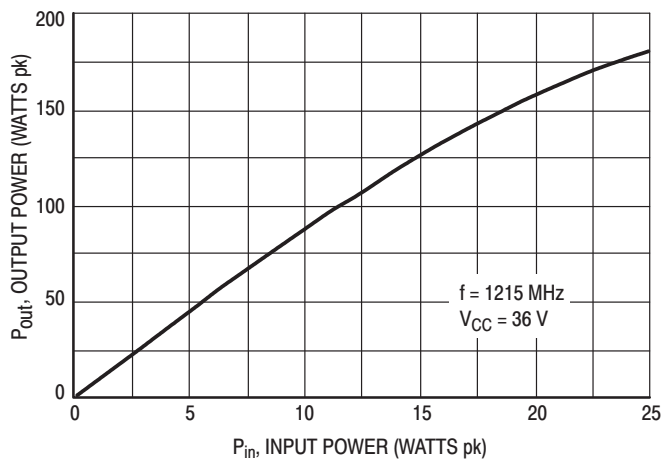


Figure 3. Output Power versus Input Power

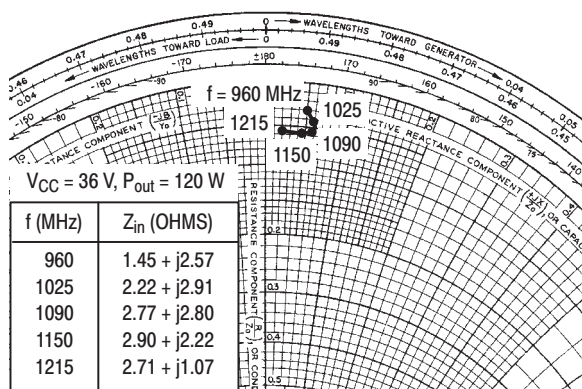
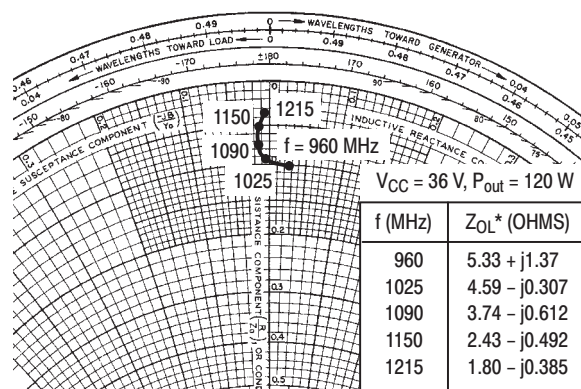


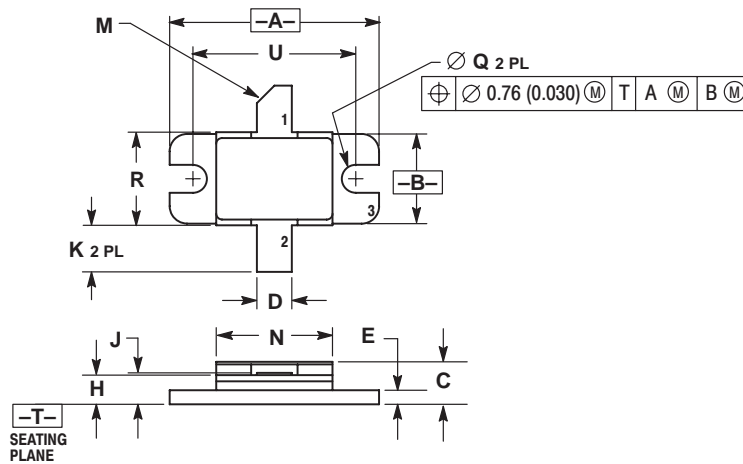
Figure 4. Series Equivalent Input Impedances



Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 5. Series Equivalent Output Impedance

PACKAGE DIMENSIONS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.890	0.910	22.61	23.11
B	0.375	0.395	9.53	10.03
C	0.150	0.165	3.81	4.19
D	0.145	0.155	3.69	3.93
E	0.055	0.065	1.40	1.65
H	0.120	0.130	3.05	3.30
J	0.003	0.006	0.08	0.15
K	0.185	0.215	4.70	5.46
M	45° REF		45° REF	
N	0.490	0.510	12.45	12.95
Q	0.115	0.125	2.93	3.17
R	0.395	0.405	10.04	10.28
U	0.700 BSC		17.78 BSC	

STYLE 1:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

CASE 355C-02 ISSUE C

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609
INTERNET: <http://Design-NET.com>

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



MRF10120/D

